

## 60V N-Channel DTMOS

Features	Product Summary
<ul style="list-style-type: none"><li>• Trench Power DTMOS Technology</li><li>• Low <math>R_{DS(ON)}</math></li><li>• Low Gate Charge</li><li>• Optimized for Fast-switching Applications</li></ul>	$V_{DS}$ 60V
	RDS(ON) (at $V_{GS}=10V$ ) < 15mΩ
	RDS(ON) (at $V_{GS}=4.5V$ ) < 19mΩ
	ID (at $V_{GS}=10V$ ) 45A
	100% UIS Tested
	
Applications	
<ul style="list-style-type: none"><li>• Synchronous Rectification in DC/DC and AC/DC Converters</li><li>• Isolated DC/DC Converters in Telecom and Industrial</li></ul>	

**Specifications**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

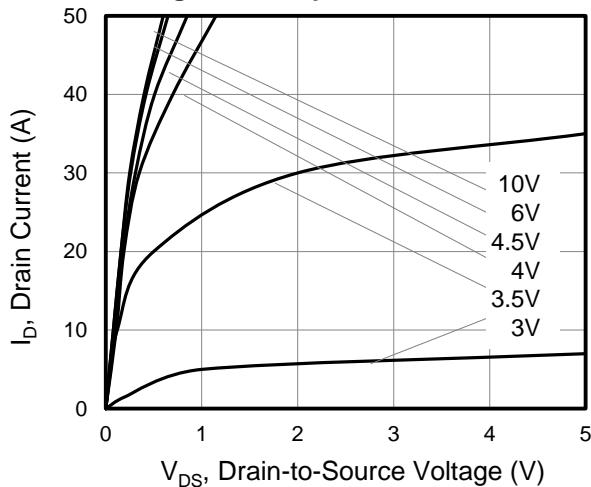
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}$ , $I_D = 250\mu\text{A}$	60	--	--	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}} = 60\text{V}$ , $V_{\text{GS}} = 0\text{V}$ , $T_J = 25^\circ\text{C}$	--	--	1	$\mu\text{A}$
		$V_{\text{DS}} = 60\text{V}$ , $V_{\text{GS}} = 0\text{V}$ , $T_J = 100^\circ\text{C}$	--	--	100	
Gate-Source Leakage	$I_{\text{GSS}}$	$V_{\text{GS}} = \pm 20\text{V}$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}$ , $I_D = 250\mu\text{A}$	1.1	--	2.5	V
Drain-Source On-Resistance (Note3)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}$ , $I_D = 20\text{A}$	--	12	15	$\text{m}\Omega$
		$V_{\text{GS}} = 4.5\text{V}$ , $I_D = 18\text{A}$	--	15	19	
Forward Transconductance (Note3)	$g_{\text{fs}}$	$V_{\text{DS}} = 5\text{V}$ , $I_D = 20\text{A}$	--	100	--	S
<b>Dynamic</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{GS}} = 0\text{V}$ , $V_{\text{DS}} = 30\text{V}$ , $f = 1.0\text{MHz}$	--	1134	--	pF
Output Capacitance	$C_{\text{oss}}$		--	123	--	
Reverse Transfer Capacitance	$C_{\text{rss}}$		--	12	--	
Total Gate Charge	$Q_g(10\text{V})$	$V_{\text{DD}} = 30\text{V}$ , $I_D = 20\text{A}$ , $V_{\text{GS}} = 10\text{V}$	--	21	--	nC
	$Q_g(4.5\text{V})$		--	11	--	
Gate-Source Charge	$Q_{\text{gs}}$		--	3.1	--	
Gate-Drain Charge	$Q_{\text{gd}}$		--	5.1	--	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 30\text{V}$ , $I_D = 20\text{A}$ , $R_G = 3\Omega$	--	7	--	ns
Turn-on Rise Time	$t_r$		--	3	--	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		--	20	--	
Turn-off Fall Time	$t_f$		--	3	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	30	A
Pulsed Diode Forward Current	$I_{\text{SM}}$		--	--	90	
Body Diode Voltage	$V_{\text{SD}}$	$T_J = 25^\circ\text{C}$ , $I_{\text{SD}} = 1\text{A}$ , $V_{\text{GS}} = 0\text{V}$	--	0.72	1	V
Reverse Recovery Time	$t_{\text{rr}}$	$I_F = 20\text{A}$ , $di_F/dt = 500\text{A}/\mu\text{s}$	--	17	--	ns
Reverse Recovery Charge	$Q_{\text{rr}}$		--	60	--	nC

**Notes**

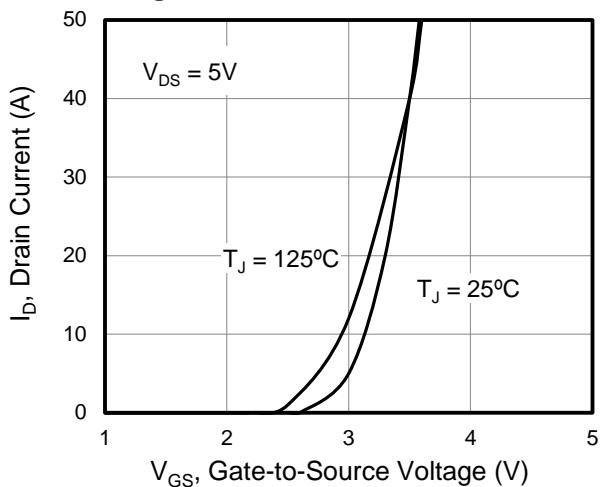
1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2.  $I_{\text{AS}} = 20\text{A}$ ,  $V_{\text{DD}} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 1\%$

**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

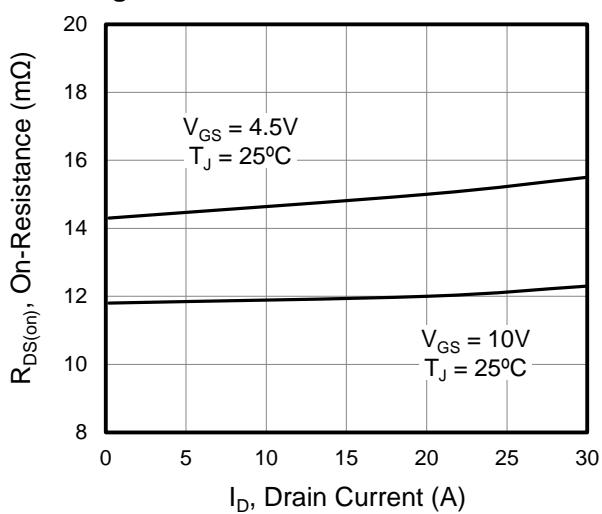
**Figure 1. Output Characteristics**



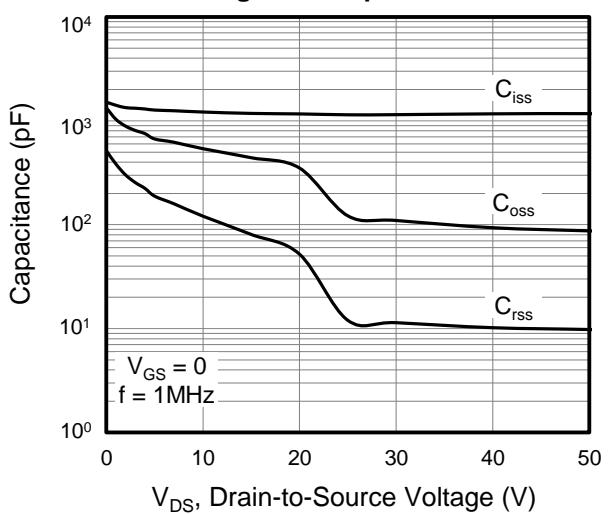
**Figure 2. Transfer Characteristics**



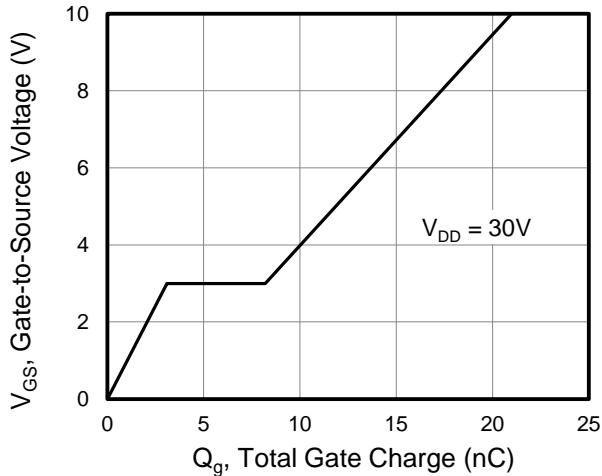
**Figure 3. On-Resistance vs. Drain Current**



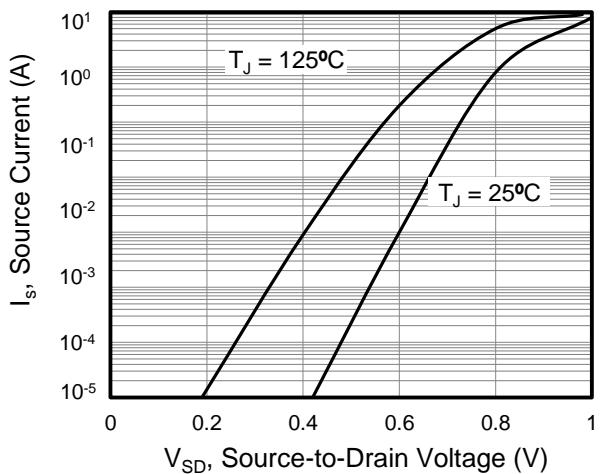
**Figure 4. Capacitance**



**Figure 5. Gate Charge**

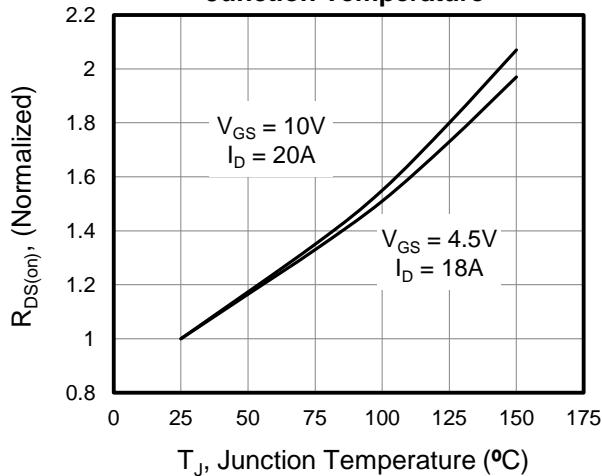


**Figure 6. Body Diode Forward Voltage**

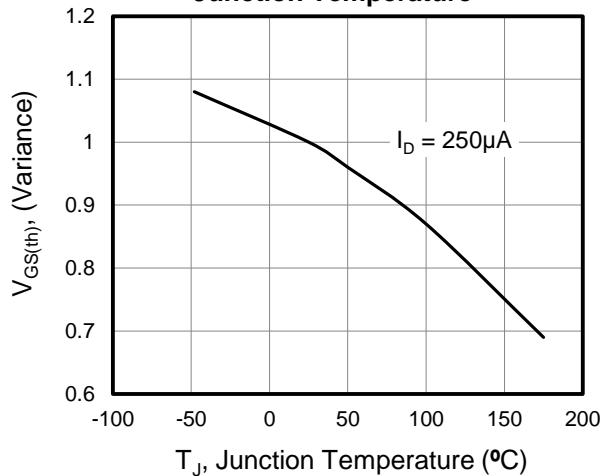


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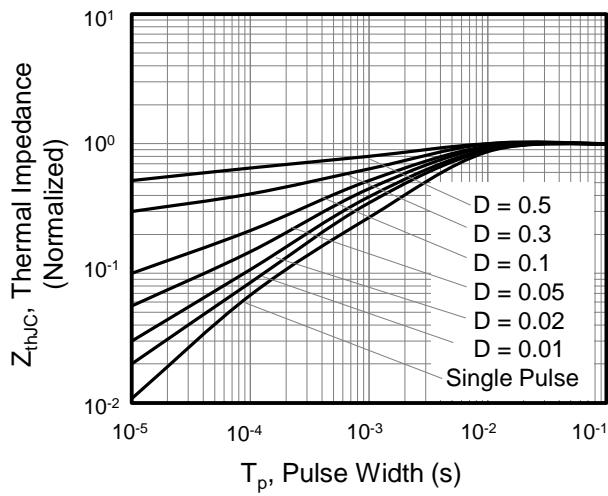
**Figure 7. On-Resistance vs. Junction Temperature**



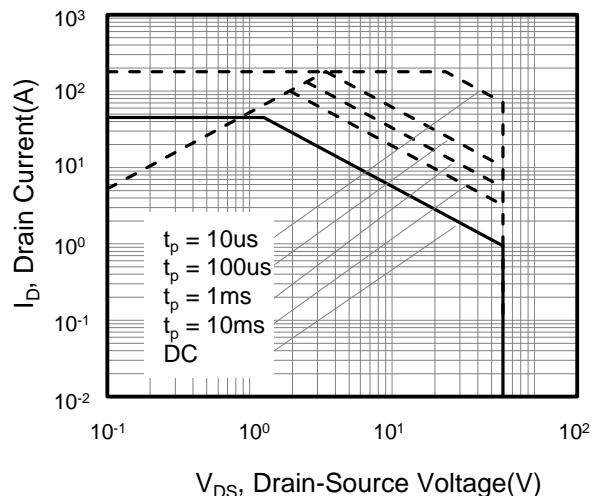
**Figure 8. Threshold Voltage vs. Junction Temperature**

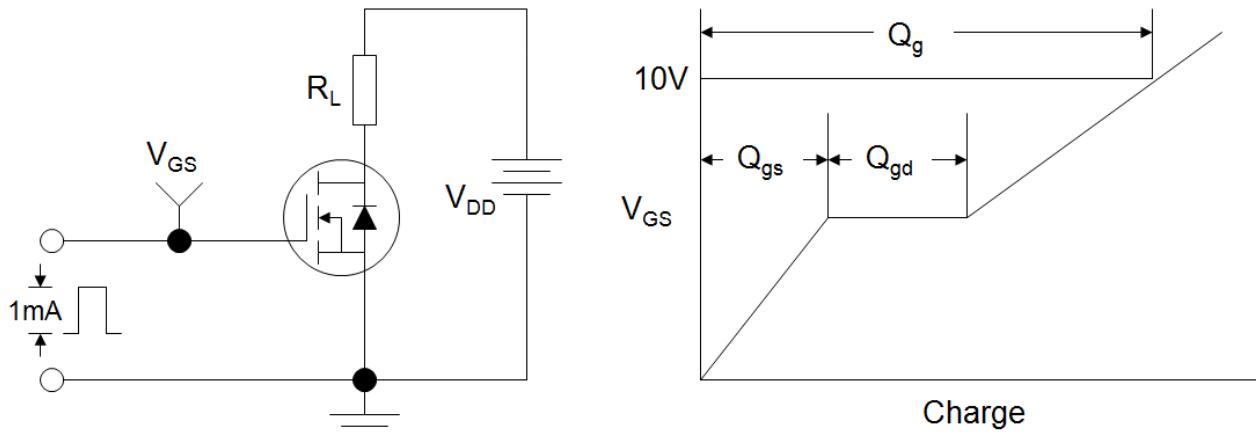
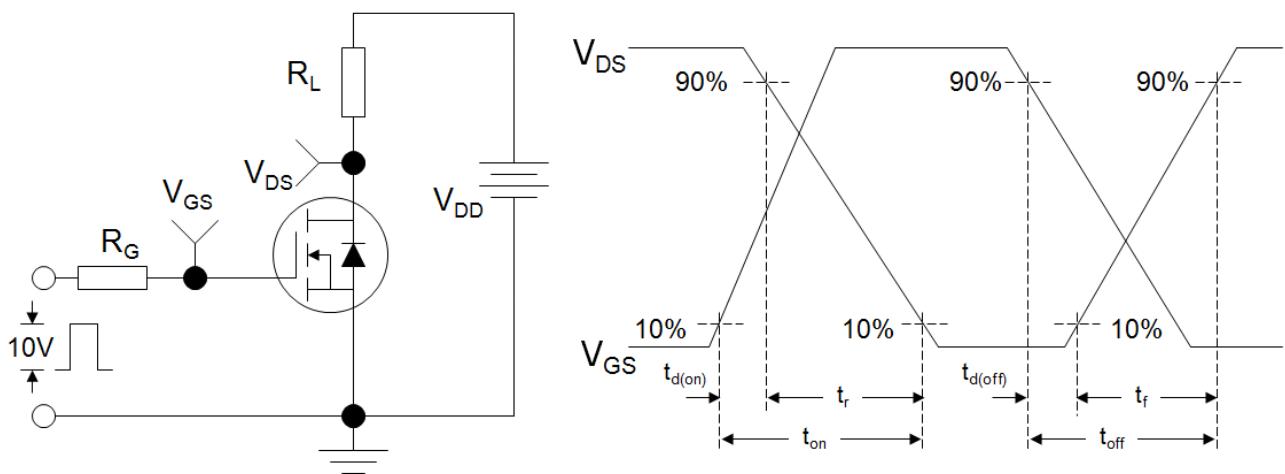
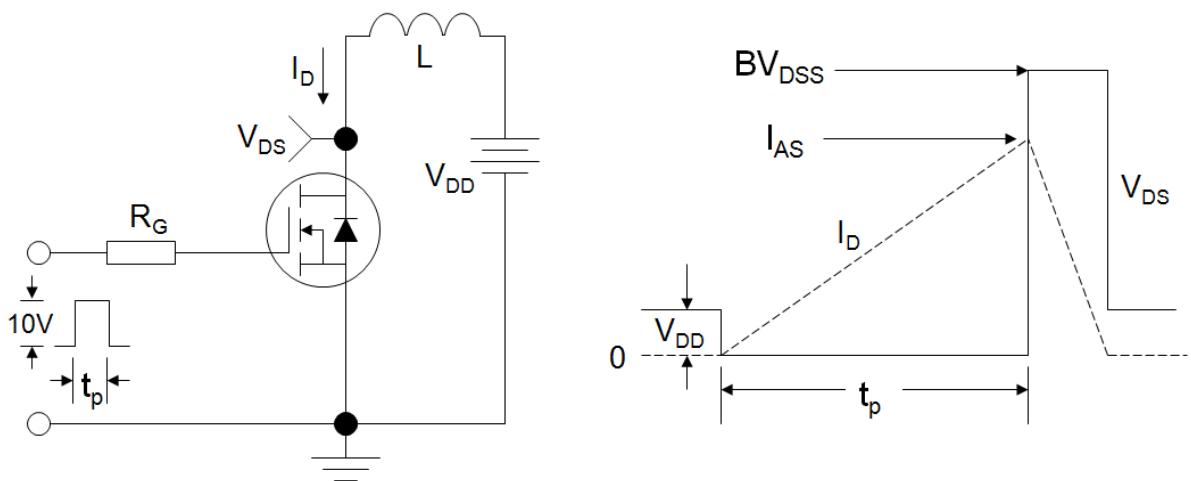


**Figure 9. Transient Thermal Impedance**

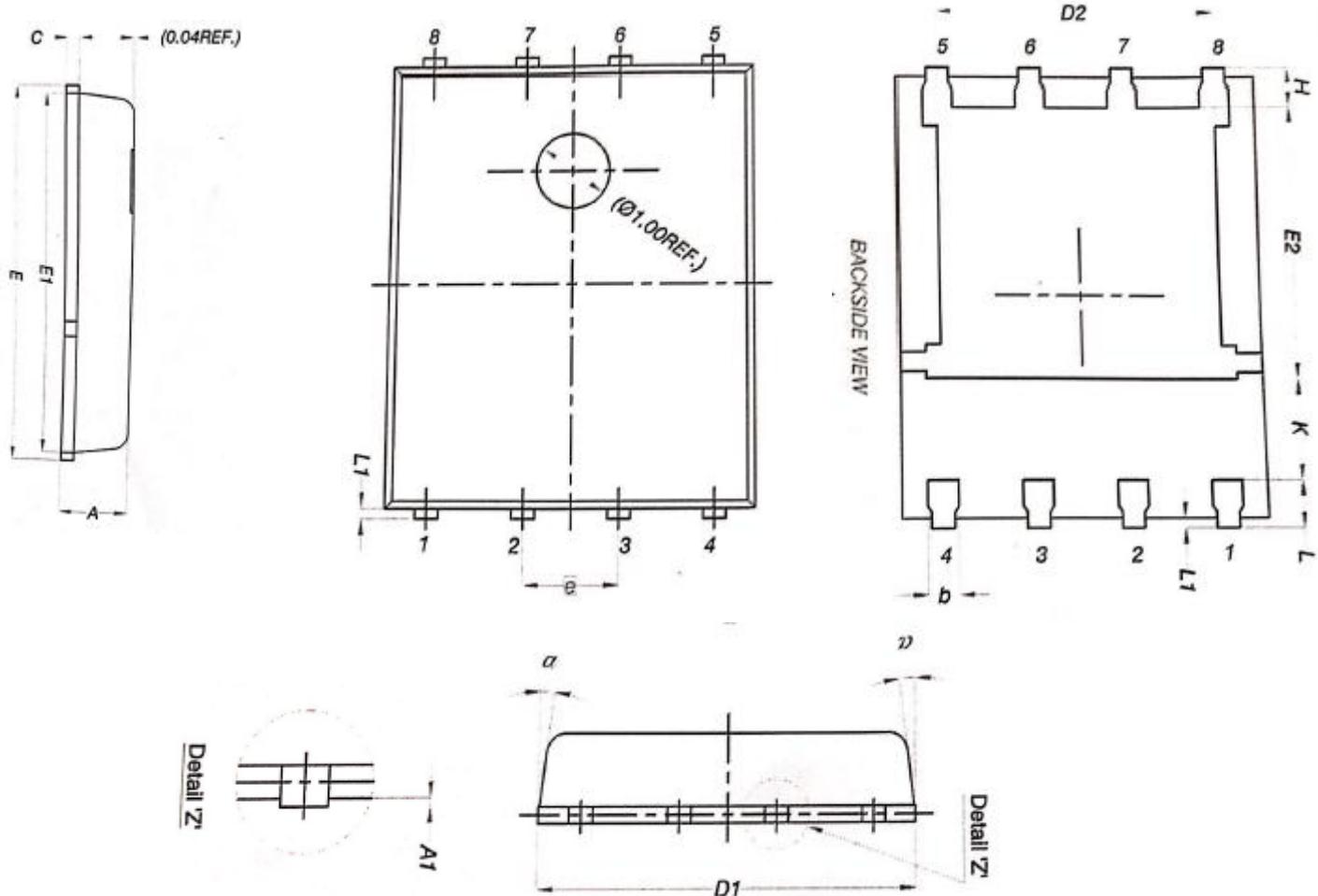


**Figure 10. Safe operation area**

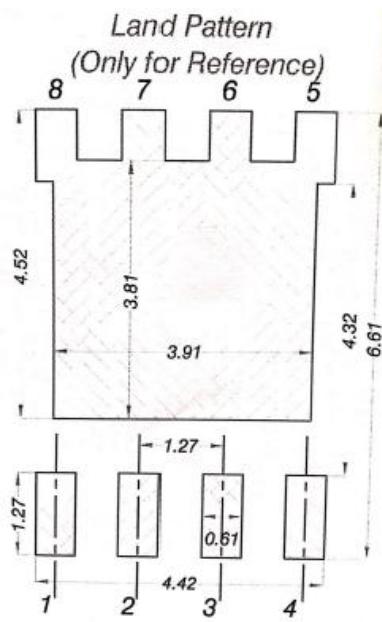


**Figure A: Gate Charge Test Circuit and Waveform**

**Figure B: Resistive Switching Test Circuit and Waveform**

**Figure C: Unclamped Inductive Switching Test Circuit and Waveform**


## DFN5×6 PACKAGR OUTLINE



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
a	0°	-	12°





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